

Schottky barrier diode

RB160L-40

●Applications

High frequency rectification
For switching power supply.

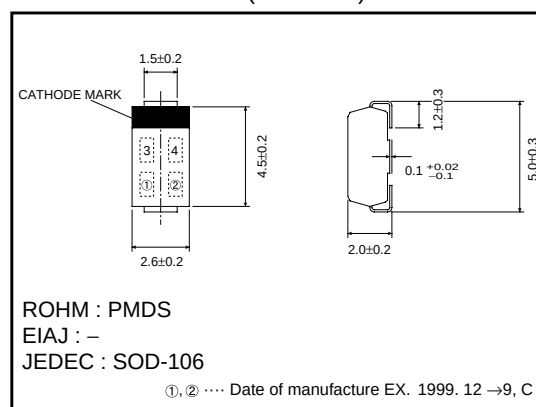
●Features

- 1) Compact power mold type (PMDS)
- 2) Low I_R . ($I_R=5\text{mA}$ Typ.)
- 3) High reliability

●Construction

Silicon epitaxial Planar

●External dimensions (Units : mm)



●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current *	I_o	1	A
Peak forward surge current	I_{FSM}	70	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40~+125	$^\circ\text{C}$

*When mounted on a PCBs board

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.55	V	$I_F = 1.0\text{A}$
Reverse current	I_R	-	-	0.1	mA	$V_R = 40\text{V}$

Diodes

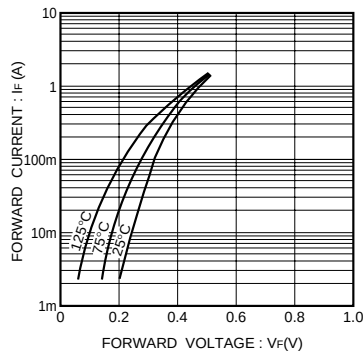
●Electrical characteristic curves ($T_a = 25^\circ\text{C}$)

Fig. 1 Forward characteristics

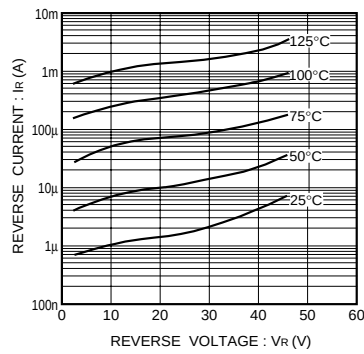


Fig. 2 Reverse characteristics

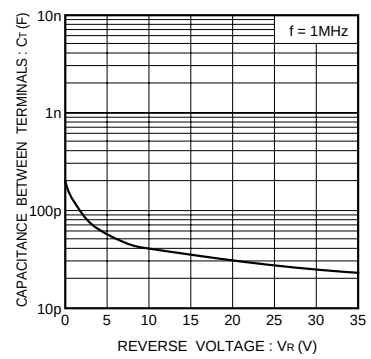


Fig. 3 Capacitance between terminals characteristics

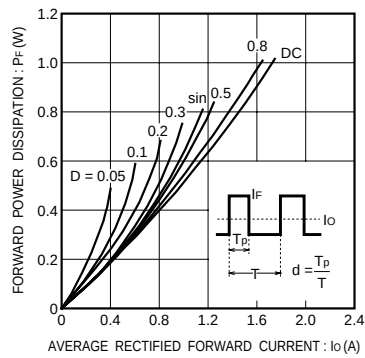


Fig. 4 Forward power dissipation characteristics

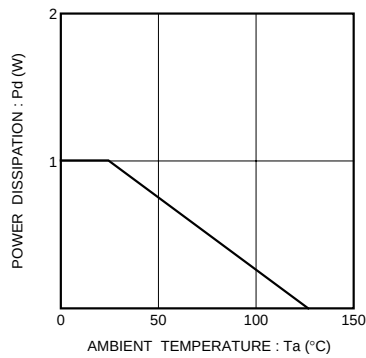


Fig. 5 Derating curve

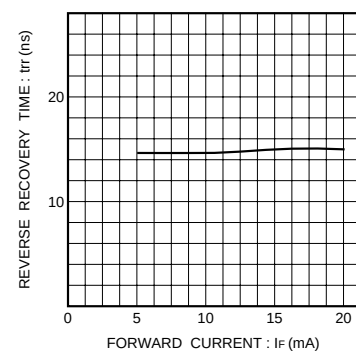


Fig. 6 Reverse recovery time characteristics